

Contact Name (Please print):

WWW. IGANPOWER.COM 230 -3410 LOUGHEED HWY VANCOUVER, BC, V5M 2A4 CANADA

EMAIL: information@iganpower.com

Application for Restricted Samples (for large current 1200V 3rd generation GaNFET)

Email and phone number:			
Organization and website:			
Type of Organization (Device manufacturer/Application-			
Solution/Unive	rsity/Other-specify):		
	or detailed description):		
•	cation (AC-DC, DC-DC, etc	c., as detailed as poss	sible):
No-Reverse	Engineering Agree	ment	
The applicant u	nderstands that the sam	ples from GaNPower	contain patent
pending design is published.	and agrees to respect th	e IP right of GaNPow	er before the patent
The Applicant f	urther agrees not to be in	nvolved in any revers	e engineering
activities on the	e samples such as x-ray, o	disassembly or peelin	g packaging
materials. The A	Applicant further agrees	not to transfer the sa	imples to anyone
outside the Organization. At evaluation/engineering stage, the applicant further			
agrees to retur	n all damaged / used san	nples to GaNPower i	frequested to do so.
Δ.,	plicant Managamant Apr	avaval /a a by Drafaa	aan in Univ
Applicant Management Approval (e.g. by Professor in Univ., Department/Division Manager or VP in Companies):			
	·	•	ies):
PII	nt Name:	Title:	
Sig	nature:	Date:	
516.1444.51			
G	GaNPower Office Notes:		